

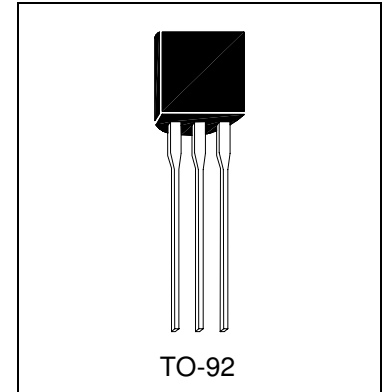


H2N5087

PNP EPITAXIAL PLANAR TRANSISTOR

Description

This device was designed for low noise, high gain, general purpose amplifier applications for 1uA to 25mA collector current.



Absolute Maximum Ratings

- Maximum Temperatures
 - Storage Temperature -55 ~ +150 °C
 - Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (T_A=25°C) 625 mW
- Maximum Voltages and Currents (T_A=25°C)
 - V_{CBO} Collector to Base Voltage -50 V
 - V_{CEO} Collector to Emitter Voltage -50 V
 - V_{EBO} Emitter to Base Voltage -3 V
 - I_C Collector Current -50mA

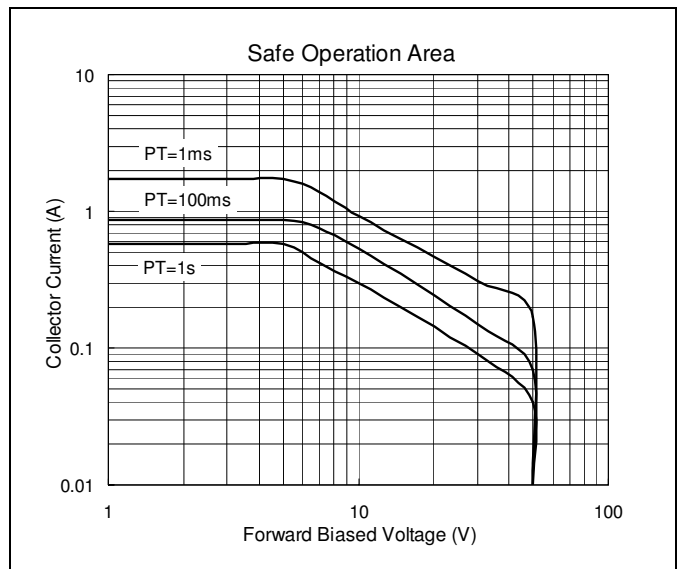
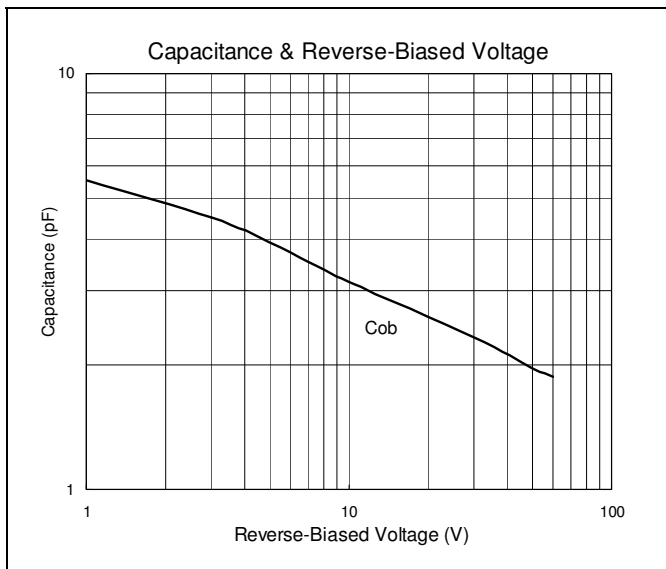
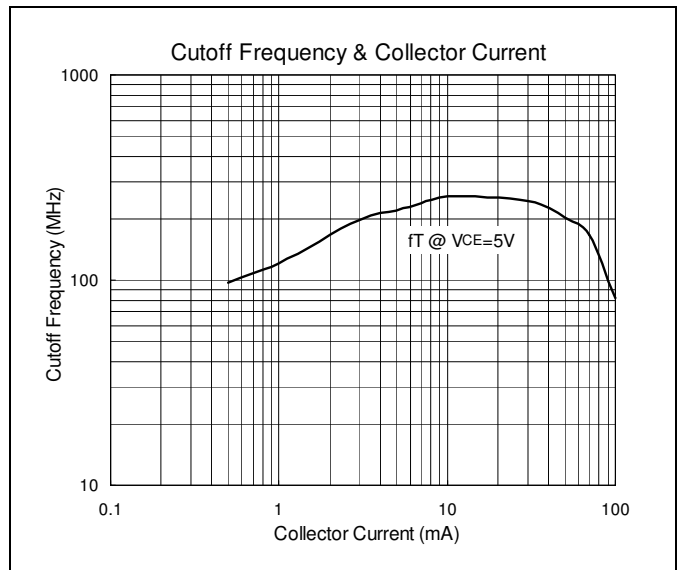
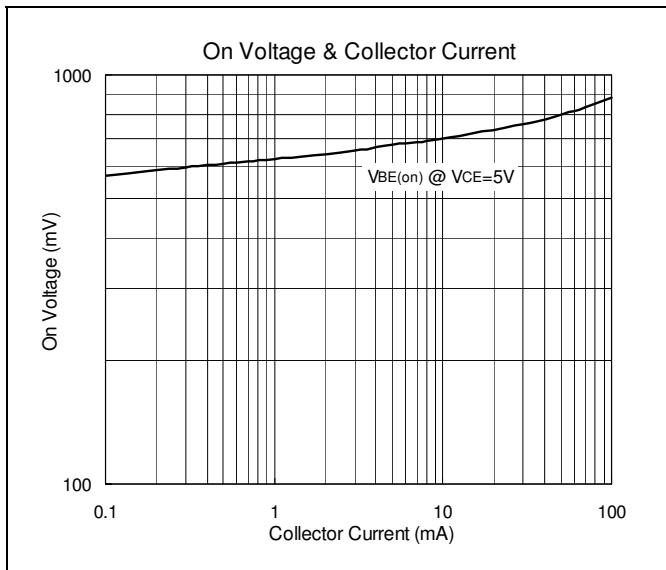
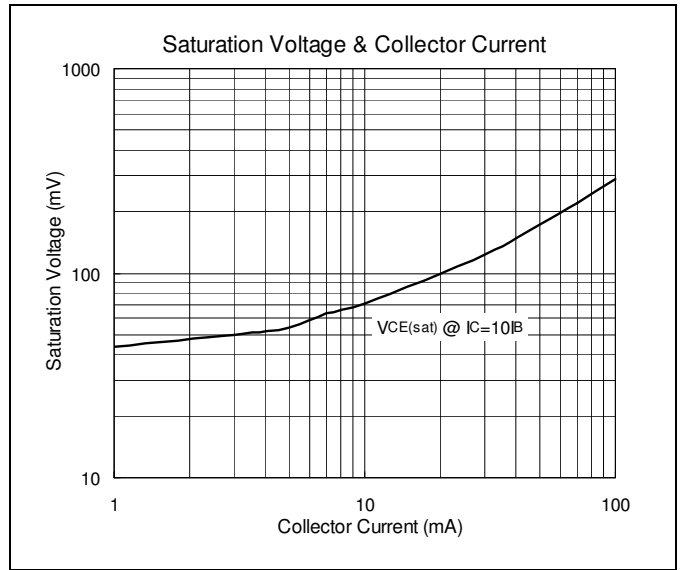
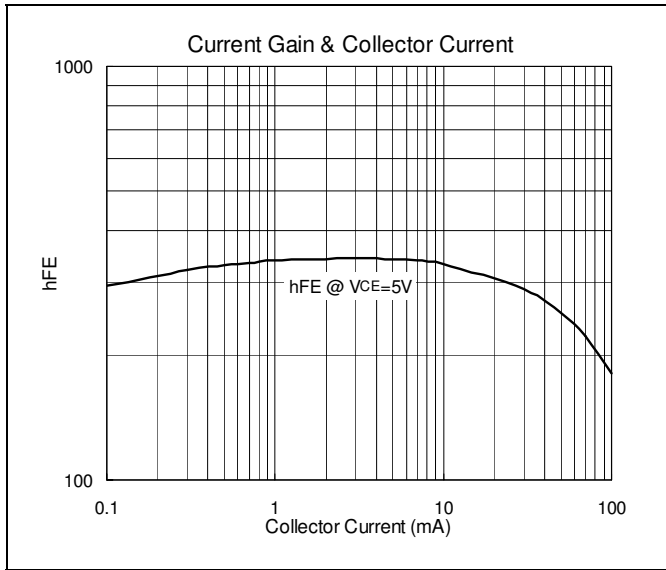
Electrical Characteristics (T_A=25°C)

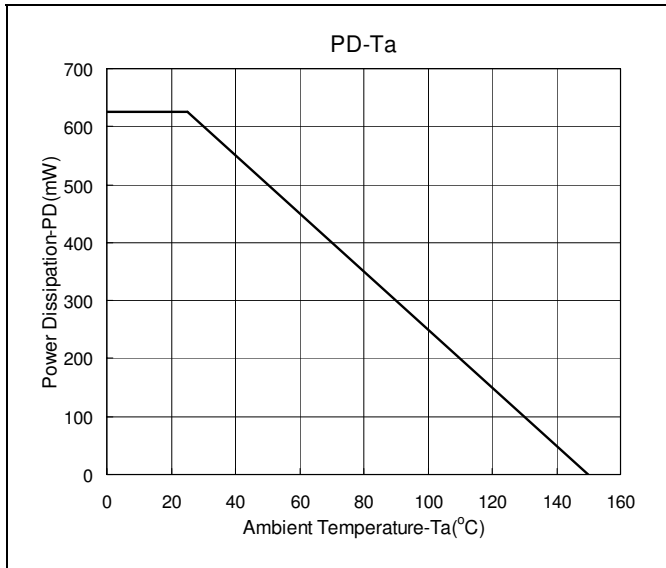
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	-50	-	-	V	I _C =-100uA
BV _{CEO}	-50	-	-	V	I _C =-1mA
BV _{EBO}	-3	-	-	V	I _E =-10uA
I _{CBO}	-	-	-50	nA	V _{CB} =-35V
I _{EBO}	-	-	-50	nA	V _{EB} =-3V
*V _{CE(sat)}	-	-	-0.3	V	I _C =-10mA, I _B =-1mA
V _{BE(on)}	-	-	-0.85	V	I _C =-10mA, I _B =-5V
*h _{FE1}	250	-	800		V _{CE} =-5V, I _C =-0.1mA
*h _{FE2}	250	-	-		V _{CE} =-5V, I _C =-1mA
*h _{FE3}	250	-	-		V _{CE} =-5V, I _C =-10mA
f _T	40	-	-	MHz	I _C =-0.5mA, V _{CE} =-5V, f=100MHz
Cob	-	-	4.0	pF	V _{CB} =-5V, f=1MHz

*Pulse Test: Pulse Width ≤380us, Duty Cycle ≤2%



Characteristics Curve







TO-92 Dimension

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

H	2	N
5	0	8
7		

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1. Emitter 2. Base 3. Collector

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	4.33	4.83
B	4.33	4.83
C	12.70	-
D	0.36	0.56
E	-	*1.27
F	3.36	3.76
G	0.36	0.56
H	-	*2.54
I	-	*1.27
$\alpha 1$	-	*5°
$\alpha 2$	-	*2°
$\alpha 3$	-	*2°

*: Typical, Unit: mm

3-Lead TO-92 Plastic Package
 HSMC Package Code: A

TO-92 Taping Dimension

DIM	Min.	Max.
A	4.33	4.83
D	3.80	4.20
D1	0.36	0.53
D2	4.33	4.83
F1, F2	2.40	2.90
H	15.50	16.50
H1	8.50	9.50
H2	-	1
H2A	-	1
H3	-	27
H4	-	21
L	-	11
L1	2.50	-
P	12.50	12.90
P1	5.95	6.75
P2	50.30	51.30
T	-	0.55
T1	-	1.42
T2	0.36	0.68
W	17.50	19.00
W1	5.00	7.00

Unit: mm

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Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _p)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T _{smin})	100°C	150°C
- Temperature Max (T _{smax})	150°C	200°C
- Time (min to max) (ts)	60~120 sec	60~180 sec
T _{smax} to T _L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t _L)	60~150 sec	60~150 sec
Peak Temperature (T _p)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t _p)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec